

Dual P-Ch 20V Fast Switching MOSFETs

- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Description

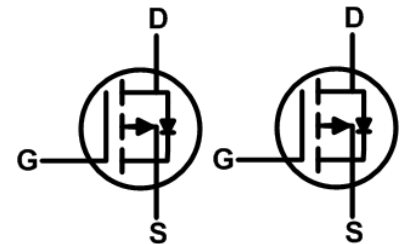
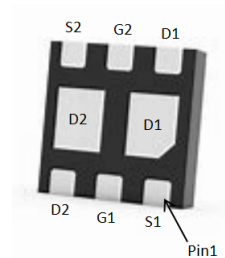
The UD3D02M is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The UD3D02M meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Product Summary

BVDSS	RDSON	ID
-20V	95mΩ	-3A

DFN2020-6L Pin Configurations



Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{DS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -4.5\text{V}^1$	-3	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -4.5\text{V}^1$	-1.4	A
I_{DM}	Pulsed Drain Current ²	-6	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	0.8	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	156	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	---	$^\circ\text{C/W}$

P-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V,I _D = -250μA	-20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -20V, V _{GS} = 0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-0.4	-0.7	-1.0	V
R _{DS(on)}	Static Drain-Source on-Resistance note2	V _{GS} =-4.5V, I _D =-2A	-	95	125	mΩ
		V _{GS} =-2.5V, I _D =-1A	-	135	190	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz	-	185	-	pF
C _{oss}	Output Capacitance		-	35	-	pF
C _{rss}	Reverse Transfer Capacitance		-	25	-	pF
Q _g	Total Gate Charge	V _{DS} = -10V, I _D = -2A, V _{GS} = -4.5V	-	2.2	-	nC
Q _{gs}	Gate-Source Charge		-	0.5	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	0.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -10V, R _L =5Ω, R _{GEN} =3Ω,V _{GS} =-4.5V,	-	10	-	ns
t _r	Turn-on Rise Time		-	30	-	ns
t _{d(off)}	Turn-off Delay Time		-	63	-	ns
t _f	Turn-off Fall Time		-	50	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-2	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-8	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = -2A	-	-	-1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

Figure 1: Output Characteristics

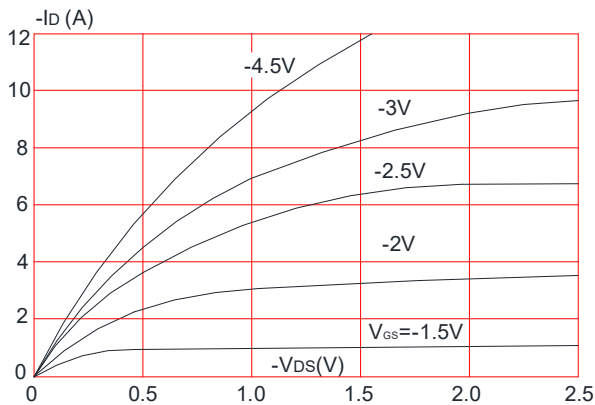


Figure 2: Typical Transfer Characteristics

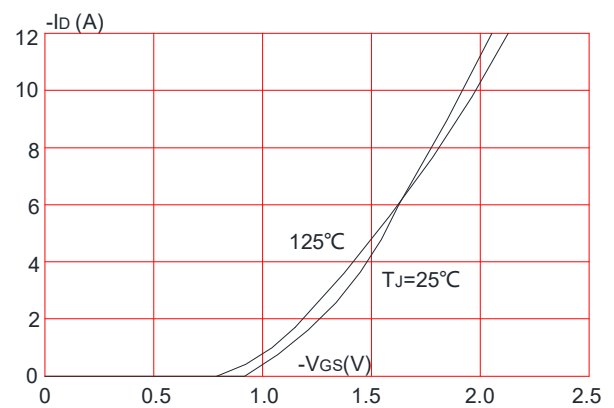


Figure 3: On-resistance vs. Drain Current

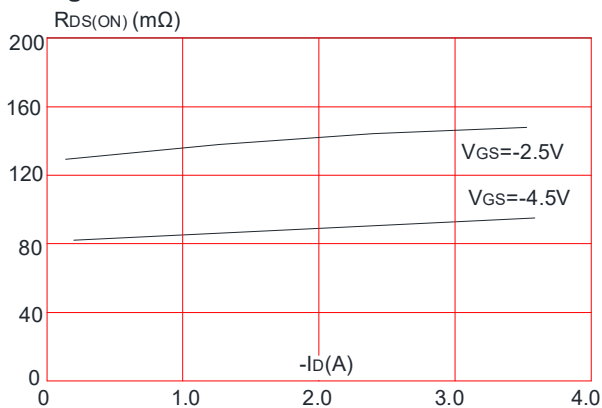


Figure 4: Body Diode Characteristics

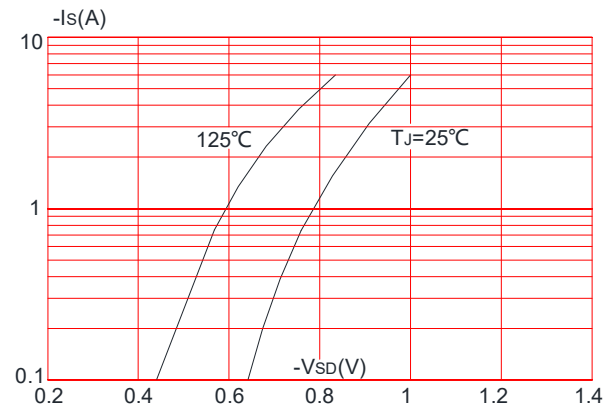


Figure 5: Gate Charge Characteristics

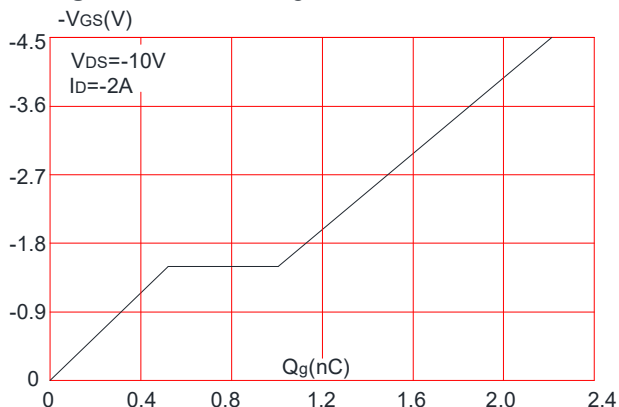


Figure 6: Capacitance Characteristics

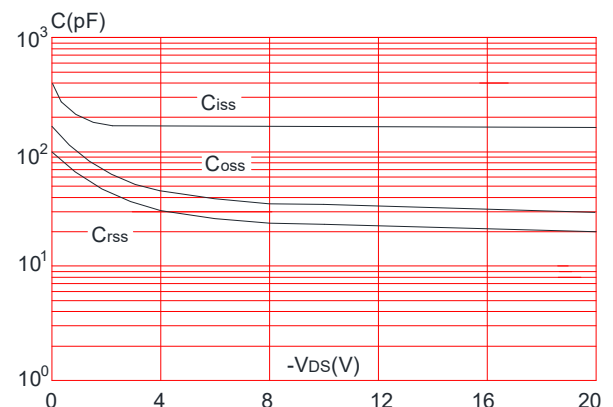


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

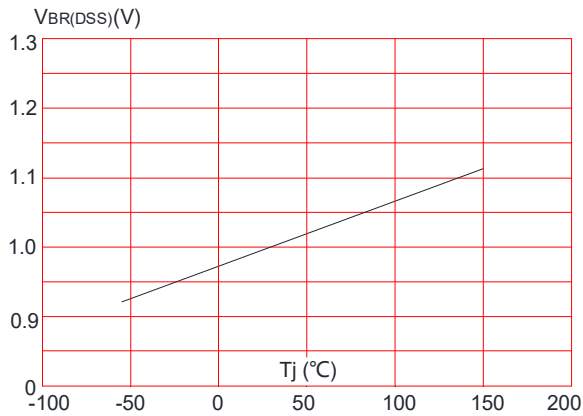


Figure 8: Normalized on Resistance vs. Junction Temperature

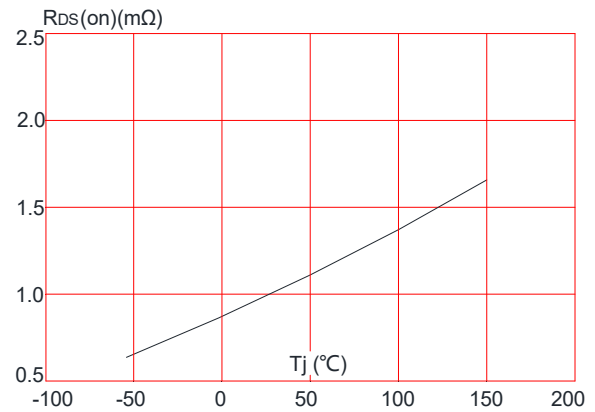


Figure 9: Maximum Safe Operating Area

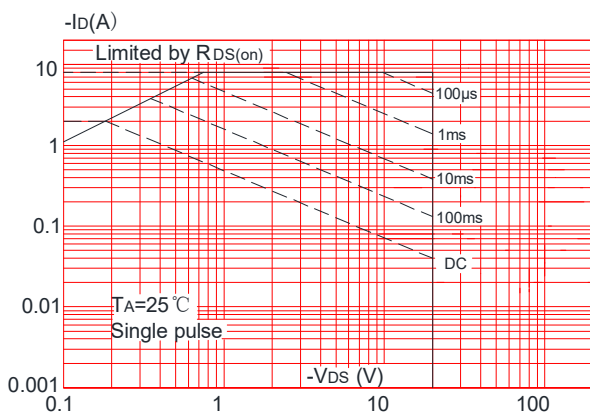


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

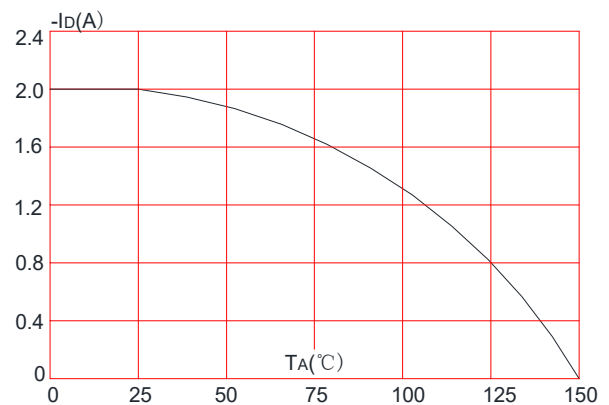
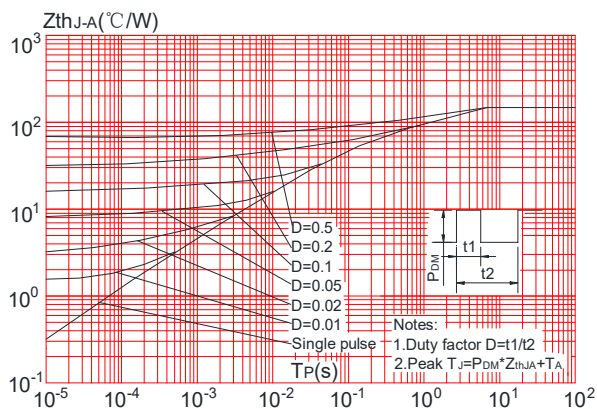
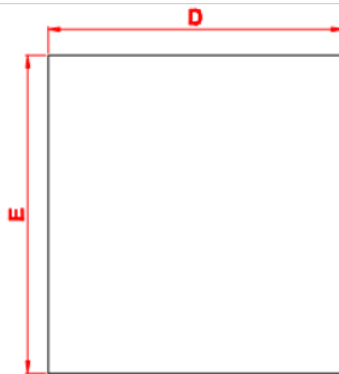


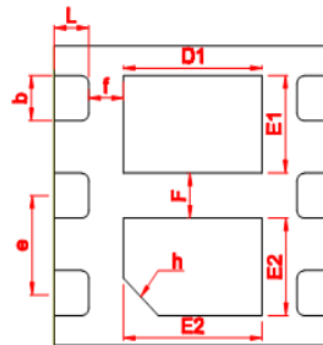
Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



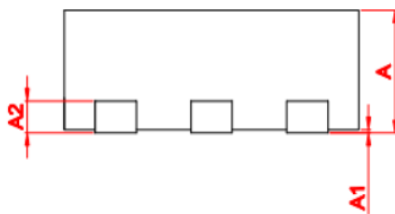
DFN2020-6L Package Information



TOP VIEW



BOTTOM VIEW



SIDE VIEW

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.700	0.750	0.800
* A1	0.000	0.020	0.050
* b	0.275	0.300	0.325
* A2	0.190	0.210	0.230
* D	1.900	2.000	2.100
* E	1.900	2.000	2.100
* E1	0.570	0.620	0.670
* E2	0.570	0.620	0.670
* D1	0.950	1.000	1.050
* D2	0.950	1.000	1.050
* e	0.600	0.650	0.700
h	0.300	0.350	0.400
* L	0.200	0.250	0.300
* F	0.250	0.300	0.350
* f	0.200	0.250	0.300